



20V P-Channel Enhancement Mode MOSFET

Voltage

-20 V

Current

-0.75 A

Features

- Low Voltage Drive (1.2V)
- Advanced Trench Process Technology
- ESD Protected
- Specially Designed for Switch Load, PWM Application, etc
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

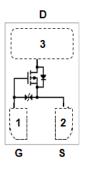
• Case: DFN1006-3L Package

• Terminals : Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.00002 ounces, 0.0007 grams







Maximum Ratings and Thermal Characteristics (T_A=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS	
PARAIVIETER				UNITS	
Drain-Source Voltage		V _{DS}	-20	V	
Gate-Source Voltage		V _{GS}	±10		
Continuous Drain Current(Note 4)		I _D	-0.75	_	
Pulsed Drain Current ^(Note 1)		I _{DM} -2		A	
Power Dissipation	T _A =25°C	Po	900	mW	
	Derate above 25°C		7.2	mW/°C	
Operating Junction and Storage Temperature Range		T _J ,T _{STG}	-55~150	°C	
Typical Thermal Resistance - Junction to Ambient, t<10s ^(Note 5)		R _{0JA}	139	°C/W	





Electrical Characteristics (T_A=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS	
Static							
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =-250uA	-20	-	-		
Gate Threshold Voltage	V _{GS(th)}	GS(th) VDS=VGS, ID=-250uA		-0.59	-1.0	V	
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =-4.5V, I _D =-400mA	-	0.85	1.2		
		V _{GS} =-2.5V, I _D =-150mA	-	0.98	1.5	Ω	
		V _{GS} =-1.8V, I _D =-80mA	-	1.15	2.2		
		V _{GS} =-1.5V, I _D =-30mA	-	1.33	3.6		
		V _{GS} =-1.2V, I _D =-10mA	-	1.5	6.0		
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-16V, V _{GS} =0V	-	-	-1	uA	
Gate-Source Leakage Current	I _{GSS}	V _{GS} =±8V, V _{DS} =0V	-	-	±10		
Dynamic ^(Note 6)							
Total Gate Charge	Qg	1011	-	1.4	-	nC	
Gate-Source Charge	Q _{gs}	V_{DS} =-10V, I_{D} =-200mA, V_{GS} =-4.5V ^(Note 2)	-	0.19	-		
Gate-Drain Charge	Q_{gd}	VGS=-4.5 V (1616 2)	-	0.2	-		
Input Capacitance	Ciss	101/11/101/	-	38	-	pF	
Output Capacitance	Coss	V _{DS} =-10V, V _{GS} =0V, f=1.0MHZ	-	15	-		
Reverse Transfer Capacitance	Crss	I=1.UIVIMZ	-	9	-		
Turn-On Delay Time	td _(on)		-	7.2	-	ns	
Turn-On Rise Time	tr	V _{DD} =-10V, I _D =-150mA,	-	21	-		
Turn-Off Delay Time	td(off)	$V_{GS}=-4.5V$, $R_{G}=6\Omega^{(Note 1,2)}$	-	85	-		
Turn-Off Fall Time	t _f	KG=012(1000 1)=)	-	116	-		
Drain-Source Diode							
Diode Forward Current	Is		-	-	-200	mA	
Diode Forward Voltage	V _{SD}	Is=-200mA, V _{GS} =0V	-	-0.93	-1.3	V	

Notes

- 1.Pulse width<300us, Duty cycle<2%.
- 2. Essentially independent of operating temperature typical characteristics.
- $3. Repetitive\ rating,\ pulse\ width\ limited\ by\ junction\ temperature\ T_J(MAX) = 150^\circ C. Ratings\ are\ based\ on\ low\ frequency\ and\ duty\ cycles\ to\ keep\ initial\ T_J=25^\circ C.$
- 4. The maximum current rating is package limited.
- 5.ReJA is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
- 6.Guaranteed by design, not subject to production testing.





TYPICAL CHARACTERISTIC CURVES

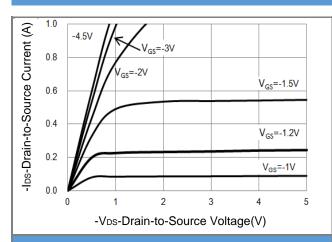


Fig.1 Output Characteristics

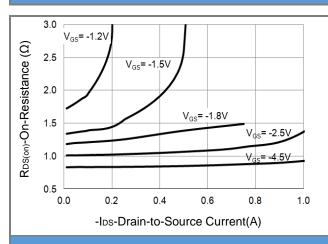


Fig.3 On-Resistance vs. Drain Current

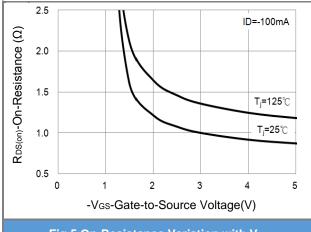


Fig.5 On-Resistance Variation with V_{GS}

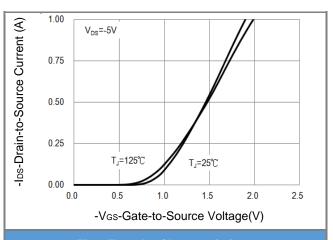


Fig.2 Transfer Characteristics

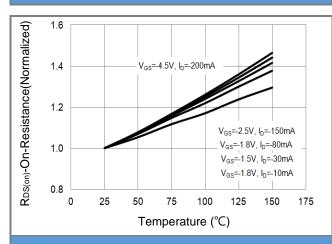


Fig.4 On-Resistance vs. Junction temperature

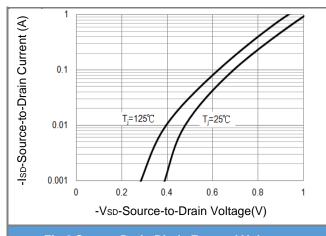


Fig.6 Source-Drain Diode Forward Voltage





TYPICAL CHARACTERISTIC CURVES

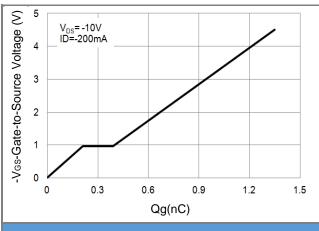


Fig.7 Gate-Charge Characteristics

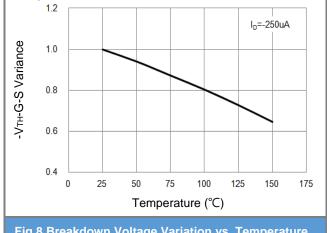


Fig.8 Breakdown Voltage Variation vs. Temperature

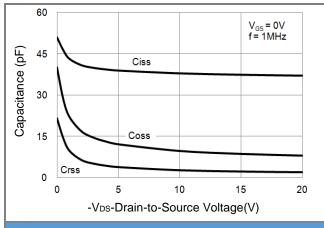


Fig.9 Capacitance vs. Drain-Source Voltage

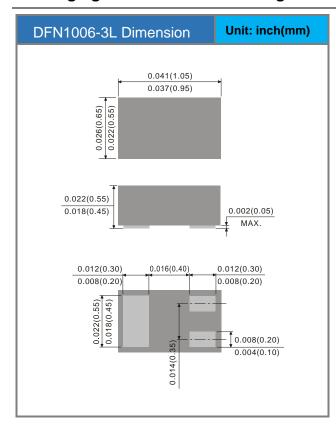


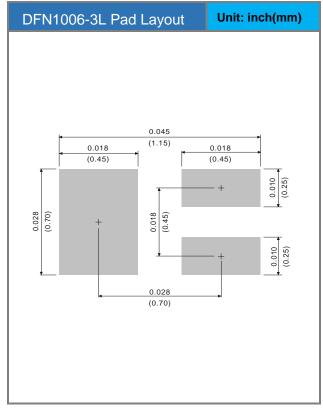


Part No. Packing Code Version

Part No. Packing Code	Package Type	Packing Type	Marking	Version
PJQ1901_R1_00201	DFN1006-3L	10K pcs / 7" reel	1	Halogen free RoHS compliant

Packaging Information & Mounting Pad Layout









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